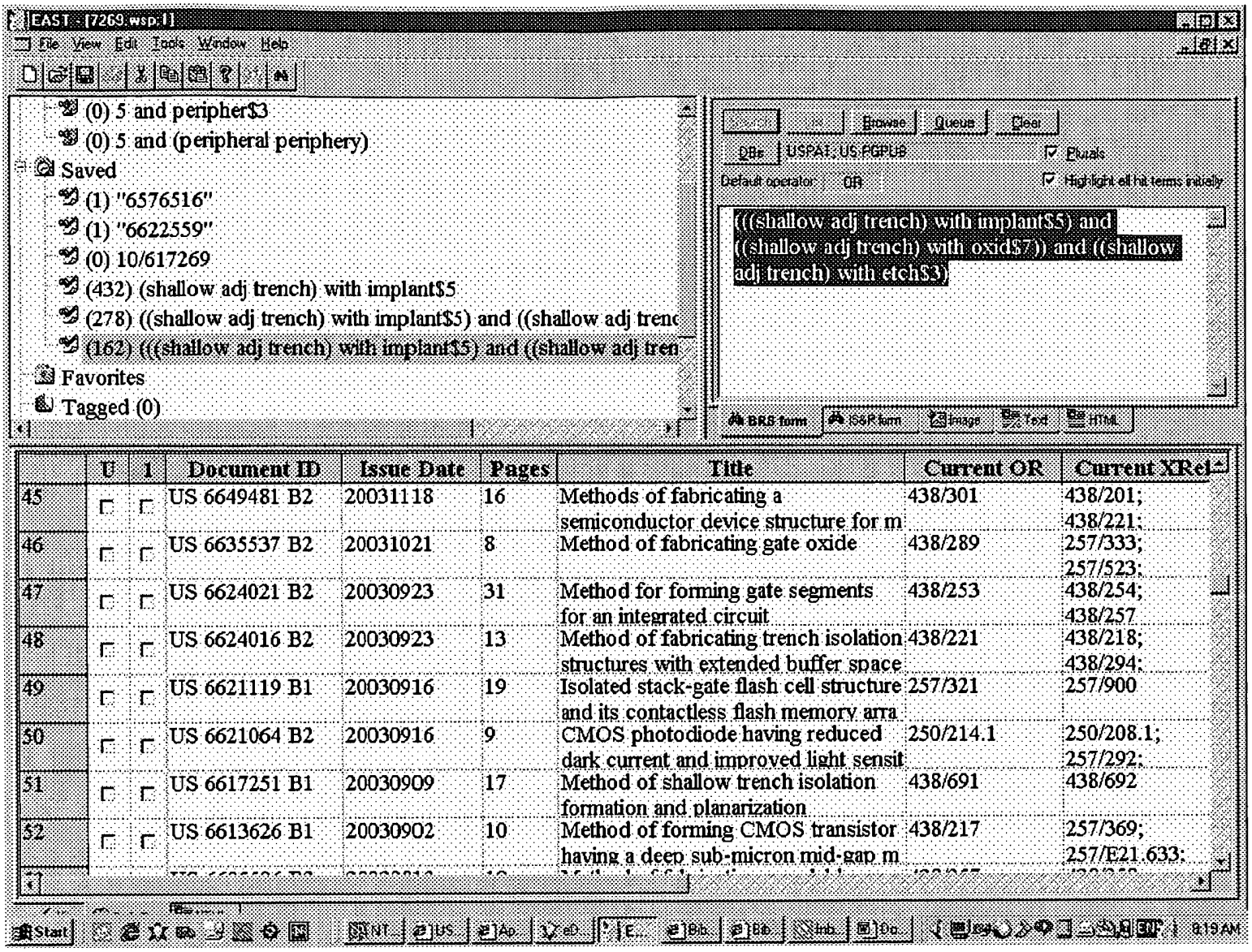
L Number	Hits	Search Text	DB	Time stamp
-	1	"6576516"	USPAT; US-PGPUB	2003/12/16 14:56
-	1	"6622559"	USPAT; US-PGPUB	2003/12/16 15:01
-	0	10/617269	USPAT; US-PGPUB	2003/12/16 16:38
-	432	(shallow adj trench) with implant$5	USPAT; US-PGPUB	2003/12/16 16:39
-	278	((shallow adj trench) with implant$5) and ((shallow adj trench) with oxid$7)	USPAT; US-PGPUB	2003/12/16 16:41
-	162	(((shallow adj trench) with implant$5) and ((shallow adj trench) with oxid$7)) and ((shallow adj trench) with etch$3)	USPAT; US-PGPUB	2003/12/16 16:54



	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRel
45	☐	☐	US 6649481 B2	20031118	16	Methods of fabricating a semiconductor device structure for m	438/301	438/201; 438/221;
46	☐	☐	US 6635537 B2	20031021	8	Method of fabricating gate oxide	438/289	257/333; 257/523;
47	☐	☐	US 6624021 B2	20030923	31	Method for forming gate segments for an integrated circuit	438/253	438/254; 438/257
48	☐	☐	US 6624016 B2	20030923	13	Method of fabricating trench isolation structures with extended buffer space	438/221	438/218; 438/294;
49	☐	☐	US 6621119 B1	20030916	19	Isolated stack-gate flash cell structure and its contactless flash memory arra	257/321	257/900
50	☐	☐	US 6621064 B2	20030916	9	CMOS photodiode having reduced dark current and improved light sensit	250/214.1	250/208.1; 257/292;
51	☐	☐	US 6617251 B1	20030909	17	Method of shallow trench isolation formation and planarization	438/691	438/692
52	☐	☐	US 6613626 B1	20030902	10	Method of forming CMOS transistor having a deep sub-micron mid-gap m	438/217	257/369; 257/E21.633;